

**Silicon NPN transistor triple diffused type
6C020**

[Applications]

High voltage

[Feature]

High voltage VCEO= 350V, VCBO= 400V

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	400	V
Collector-emitter voltage	VCEO	350	V
Emitter-base voltage	VEBO	7	V
Collector current	IC	100	mA
Junction temperature	Tj	125	C
Storage temperature	Tstg	-55 to 125	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	400	-	-	V	IC= 50uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	350	-	-	V	IC= 10mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	7	-	-	V	IE= 50uA, IC= 0A
Collector cutoff current	ICBO	-	-	10	uA	VCB= 300V
DC current gain	hFE	30	-	333	-	VCE= 10V, IC= 10mA
Collector-emitter saturation voltage	VCE(sat)	-	-	0.5	V	IC= 10mA, IB= 1mA

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

